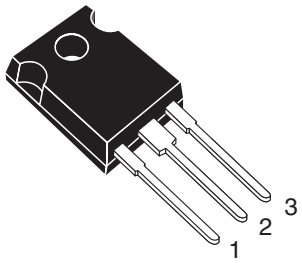
STGW45HF60WD

45 A, 600 V ultra fast IGBT

Preliminary data

Features

- Improved E_{off} at elevated temperature
- Low C_{RES} / C_{IES} ratio (no cross-conduction susceptibility)
- Ultra fast soft recovery antiparallel diode



TO-247

Applications

- Welding
- Induction heating
- High frequency converters
- Power factor correction

Description

The "HF" series is based on a new planar technology concept to yield an IGBT with tighter variation of switching energy (E_{off}) versus temperature. Suffix "W" denotes a subset of products tailored to high switching frequency operation over 100 kHz.

Figure 1. Internal schematic diagram

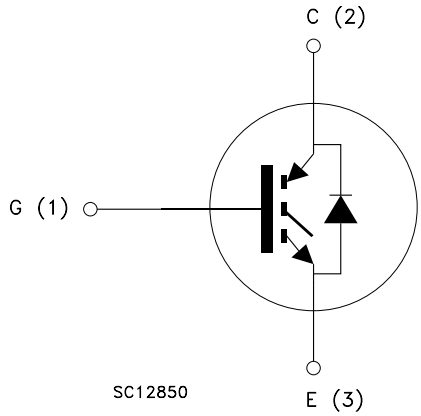


Table 1. Device summary

Order code	Marking	Package	Packaging
STGW45HF60WD	GW45HF60WD	TO-247	Tube

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage (V_{GE} = 0)	600	V
I_C (1)	Continuous collector current at T_C = 25 °C	70	A
I_C (1)	Continuous collector current at T_C = 100 °C	45	A
I_{CP}(2)	Collector current (pulsed)	TBD	A
I_{CL} (3)	Turn-off latching current	TBD	A
V_{GE}	Gate-emitter voltage	± 20	V
I_F	Diode RMS forward current at T_C = 25 °C	30	A
I_{FSM}	Surge not repetitive forward current t_p= 10 ms sinusoidal	120	A
P_{TOT}	Total dissipation at T_C = 25 °C	250	W
T_{stg}	Storage temperature	– 55 to 150	°C
T_j	Operating junction temperature		

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

2. Pulse width limited by max junction temperature
3. V_{CLAMP} = 80% (V_{CES}), V_{GE} = 15 V, R_G = 10 Ω, T_J = 150 °C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case IGBT	0.5	°C/W
	Thermal resistance junction-case diode	1.5	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient	50	°C/W

2 Electrical characteristics

(T_J = 25 °C unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage (V_{GE} = 0)	I_C = 1 mA	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15 V, I_C= 30 A V_{GE} = 15V, I_C = 30 A,T_J= 125 °C		1.9 TBD	2.5	V V
$V_{GE(th)}$	Gate threshold voltage	V_{CE} = V_{GE}, I_C = 250µA	3.75		5.75	V
I_{CES}	Collector cut-off current (V_{GE} = 0)	V_{CE} = 600 V V_{CE} = 600 V, T_J = 125 °C			500 5	µA mA
I_{GES}	Gate-emitter leakage current (V_{CE} = 0)	V_{GE} = ±20 V			± 100	nA
g_{fs}	Forward transconductance	V_{CE} = 15 V, I_C = 30 A		TBD		S

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies} C_{oes} C_{res}	Input capacitance Output capacitance Reverse transfer capacitance	V_{CE} = 25 V, f = 1 MHz, V_{GE} = 0	-	TBD TBD TBD	-	pF pF pF
Q_g Q_{ge} Q_{gc}	Total gate charge Gate-emitter charge Gate-collector charge	V_{CE} = 390 V, I_C = 30 A, V_{GE} = 15 V, *Figure 3*	-	TBD TBD TBD	-	nC nC nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 390 V, I_C = 30 A R_G = 10 Ω, V_{GE} = 15 V, *Figure 2*	-	TBD TBD TBD	-	ns ns A/µs
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 390 V, I_C = 30 A R_G = 10 Ω, V_{GE} = 15 V, T_J = 125 °C *Figure 2*	-	TBD TBD TBD	-	ns ns A/µs
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	V_{CC} = 390 V, I_C = 30 A, R_{GE} = 10 Ω, V_{GE} = 15 V *Figure 2*	-	TBD TBD TBD	-	ns ns ns
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	V_{CC} = 390 V, I_C = 30 A, R_{GE} = 10 Ω, V_{GE} =15 V, T_J = 125 °C *Figure 2*	-	TBD TBD TBD	-	ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on} (1) E_{off} E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	V_{CC} = 390 V, I_C = 30 A R_G = 10 Ω, V_{GE} = 15 V, *Figure 4*	-	300 250 550		µJ µJ µJ
E_{on} (1) E_{off} E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	V_{CC} = 390 V, I_C = 30 A R_G = 10 Ω, V_{GE} = 15 V, T_J = 125 °C *Figure 4*	-	550 500 1050	750	µJ µJ µJ

1. Eon is the tun-on losses when a typical diode is used in the test circuit in *Figure 4*. If the IGBT is offered in a package with a co-pak diode, the co-pack diode is used as external diode. IGBTs & Diode are at the same temperature (25 °C and 125 °C). Eon include diode recovery energy.

Table 8. Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on-voltage	I_F = 30 A I_F = 30 A, T_J = 125 °C	-	1.6 1.4	-	V V
t_{rr} Q_{rr} I_{rrm}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_F = 30 A,V_R = 50 V, di/dt = 100 A/µs *(see Figure 5)*	-	45 56 2.55	-	ns nC A
t_{rr} Q_{rr} I_{rrm}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_F = 30 A,V_R = 50 V, di/dt = 100 A/µs T_J =125 °C, *(see Figure 5)*	-	100 290 5.8	-	ns nC A

3 Test circuits

Figure 2. Test circuit for inductive load switching

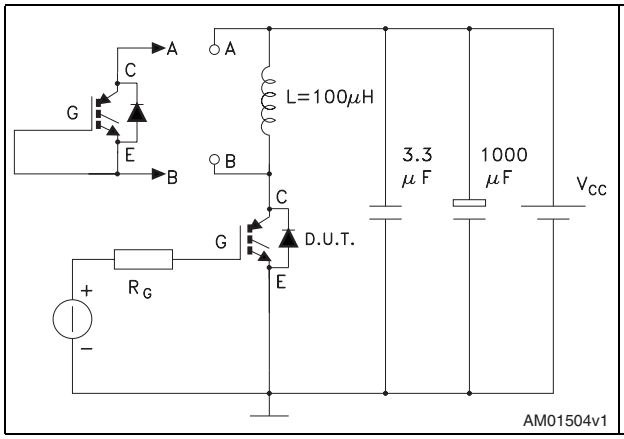


Figure 3. Gate charge test circuit

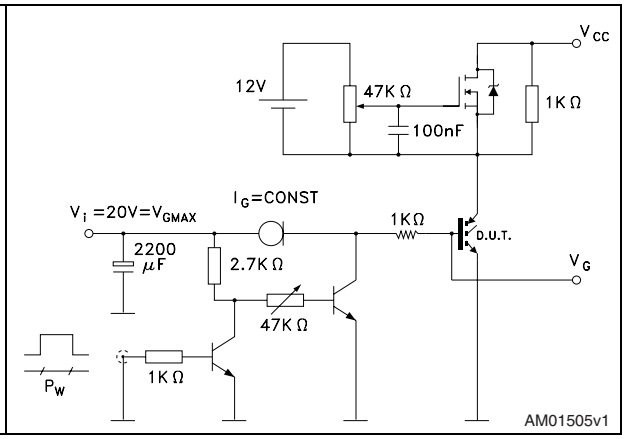


Figure 4. Switching waveform

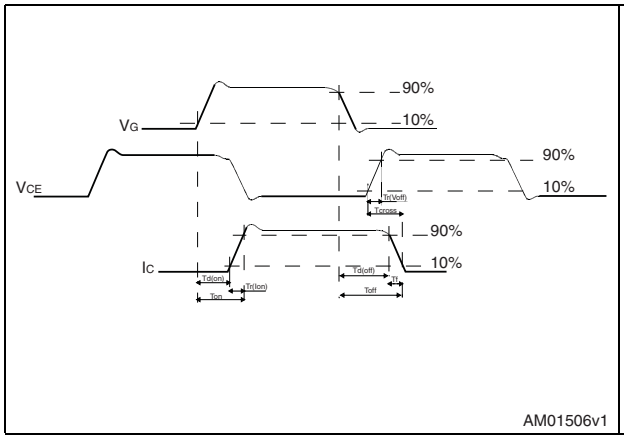
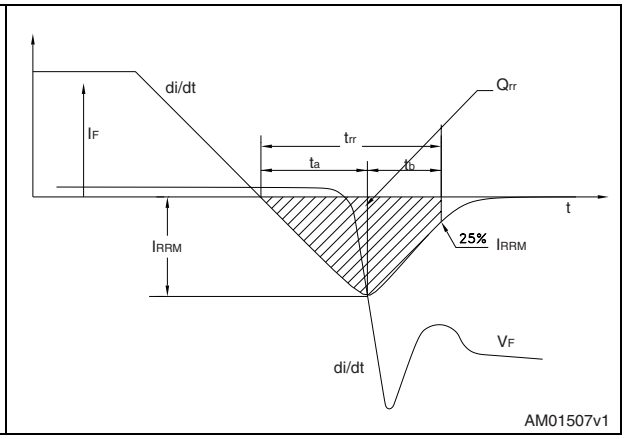


Figure 5. Diode recovery time waveform

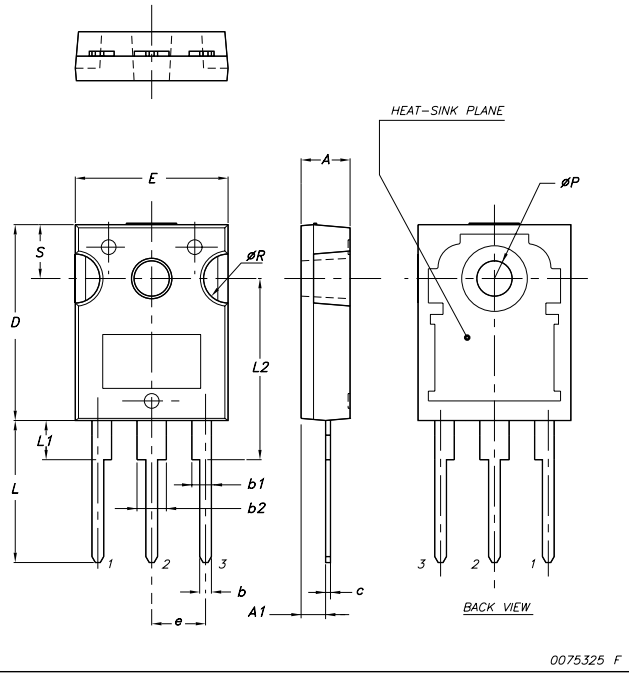


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
16-Apr-2009	1	Initial release.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST’s terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST’S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER’S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com